Special Issue on Beyond Moore: Resistive Switching Devices for Emerging Memory and **Neuromorphic Computing**

■ RESEARCH HIGHLIGHTS

010201	Ion migration in	perovskite solar cells
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Xiaoxue Ren, Lixiu Zhang, Yongbo Yuan, and Liming Ding [4 pages]

■ COMMENTS AND OPINIONS

010301	Embracing the era of neuromorphic computing
[3 pages]	Yanghao Wang, Yuchao Yang, Yue Hao, and Ru Huang

A pioneer in magnetic semiconductors — Professor Stephan von Molnár 010302

Jianhua Zhao, Yongqing Li, and Peng Xiong [3 pages]

■ SHORT COMMUNICATION

010501	A chlorinated copolymer donor demonstrates a 18.13% power conversion	n
	efficiency	

Jianqiang Qin, Lixiu Zhang, Chuantian Zuo, Zuo Xiao, Yongbo Yuan, Shangfeng Yang, Feng Hao, Ming Cheng, [5 pages] Kuan Sun, Qinye Bao, Zhengyang Bin, Zhiwen Jin, and Liming Ding

D18, an eximious solar polymer! 010502

Ke Jin, Zuo Xiao, and Liming Ding [5 pages]

■ EDITORIAL

Preface to the Special Issue on Beyond Moore: Resistive Switching Devices for 010101 **Emerging Memory and Neuromorphic Computing**

Yue Hao, Huaqiang Wu, Yuchao Yang, Qi Liu, Xiao Gong, Genquan Han, and Ming Li [2 pages]

REVIEWS

013101	Towards engineering in memristors for emerging memory and neuromorphic
	computing: A review

Andrey S. Sokolov, Haider Abbas, Yawar Abbas, and Changhwan Choi [29 pages]

A review of in situ transmission electron microscopy study on the switching 013102 mechanism and packaging reliability in non-volatile memory

Xin Yang, Chen Luo, Xiyue Tian, Fang Liang, Yin Xia, Xinqian Chen, Chaolun Wang, Steve Xin Liang, [15 pages] Xing Wu, and Junhao Chu

Electrolyte-gated transistors for neuromorphic applications 013103

Heyi Huang, Chen Ge, Zhuohui Liu, Hai Zhong, Erjia Guo, Meng He, Can Wang, [13 pages] Guozhen Yang, and Kuijuan Jin



013104	Multiply accumulate operations in memristor crossbar arrays for analog computing
[22 pages]	Jia Chen, Jiancong Li, Yi Li, and Xiangshui Miao

013105 Neuromorphic vision sensors: Principle, progress and perspectives

[10 pages] Fuyou Liao, Feichi Zhou, and Yang Chai

■ ARTICLES

[6 pages]

014101	Study of short-term synaptic plasticity in Ion-Gel gated graphene electric-double-layer synaptic transistors
[6 pages]	Chenrong Gong, Lin Chen, Weihua Liu, and Guohe Zhang
014102	Voltage-dependent plasticity and image Boolean operations realized in a WO _x -based memristive synapse
[6 pages]	Jiajuan Shi, Ya Lin, Tao Zeng, Zhongqiang Wang, Xiaoning Zhao, Haiyang Xu, and Yichun Liu
014103	Neutron irradiation-induced effects on the reliability performance of electrochemical metallization memory devices

Ye Tao, Xuhong Li, Zhongqiang Wang, Gang Li, Haiyang Xu, Xiaoning Zhao, Ya Lin, and Yichun Liu